

DESCRIPTION

The MXN3347 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a load switch or in PWM applications.

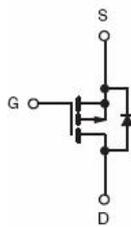
GENERAL FEATURES

- $V_{DS}=-30V$, $I_D=-35A$
 $R_{DS(ON)}(Typ.)=13.5m\Omega @ V_{GS}=-4.5V$
 $R_{DS(ON)}(Typ.)=9m\Omega @ V_{GS}=-10V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

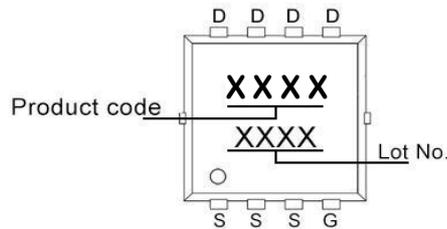
APPLICATION

- PWM applications
- Load switch
- Power management

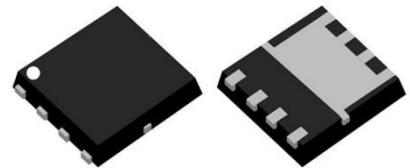
PINOUT



Schematic diagram



Marking and pin Assignment



DFN3X3-8L view

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MXN3347	-55°C to 150°C	DFN3X3-8L	5000

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_C=25^\circ C$)	I_D	-35	A
Drain Current-Pulsed ^(Note1)	I_{DM}	-90	A
Drain Current-Continuous	I_{DSM}	-13	A
Maximum Power Dissipation	P_{DSM}	3.1	W
Maximum Power Dissipation ($T_C=25^\circ C$)	P_D	29	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	40	$^\circ C/W$
Thermal Resistance, Junction-to-Case, Steady State	$R_{\theta JC}$	4.2	$^\circ C/W$

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.



ELECTRICAL CHARACTERISTICS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
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Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

On Characteristics(Note3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.4	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-7A$	-	13.5	16	$m\Omega$
		$V_{GS}=-10V, I_D=-8A$	-	9	12	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-10A$	20	-	-	S

Dynamic Characteristics(Note4)

Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, F=1.0MHz$	-	1200	-	pF
Output Capacitance	C_{oss}		-	200	-	pF
Reverse Transfer Capacitance	C_{rss}		-	150	-	pF

Switching Characteristics(Note4)

Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=-15V, I_D=-10A, V_{GS}=-10V, R_{GEN}=1\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	6	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-10A, V_{GS}=-10V$	-	25	-	nC
Gate-Source Charge	Q_{gs}		-	3.9	-	nC
Gate-Drain Charge	Q_{gd}		-	4.8	-	nC

Drain-Source Diode Characteristics

Diode Forward Voltage ^(Note3)	V_{SD}	$V_{GS}=0V, I_S=-2A$	-0.4	-	-1.0	V
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Note 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Note 4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 1. Switching Test Circuit

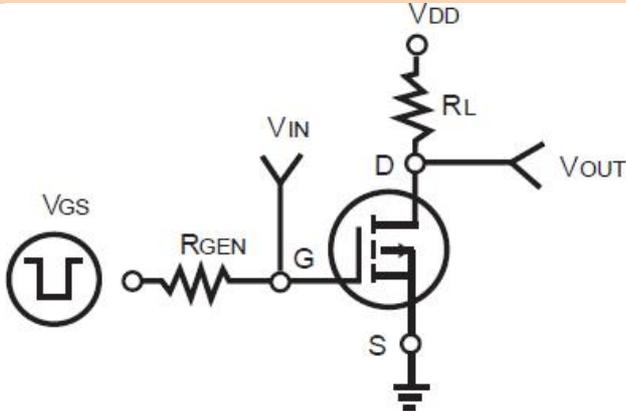


Figure 2. Switching Waveform

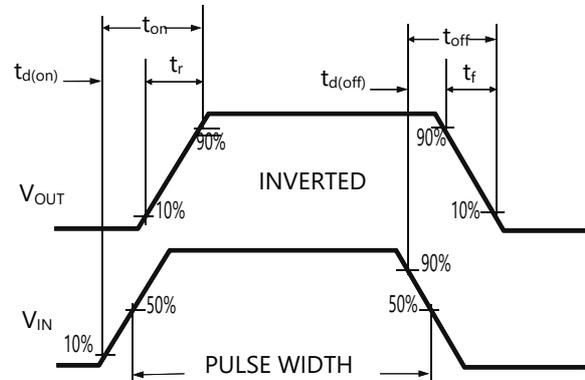


Figure 3. Power Dissipation

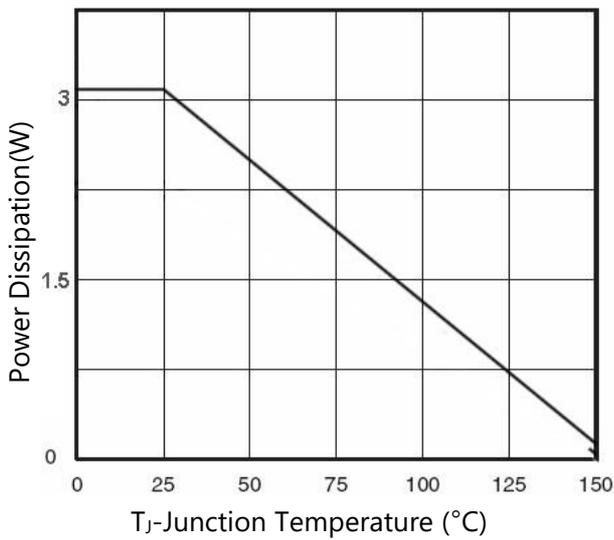


Figure 4. Drain Current

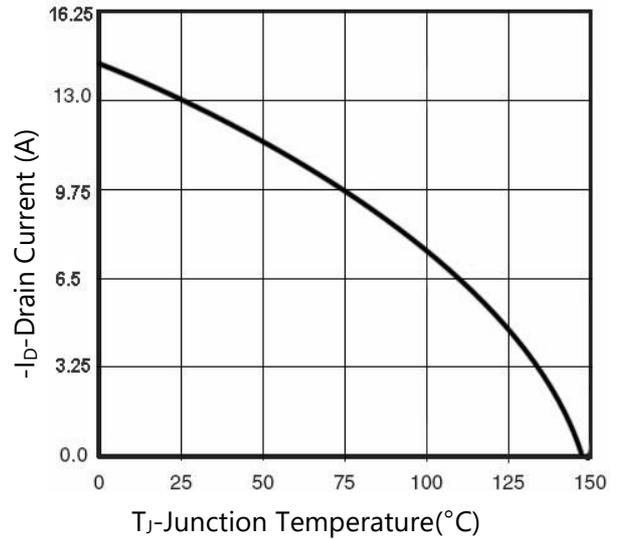


Figure 5. Output Characteristics

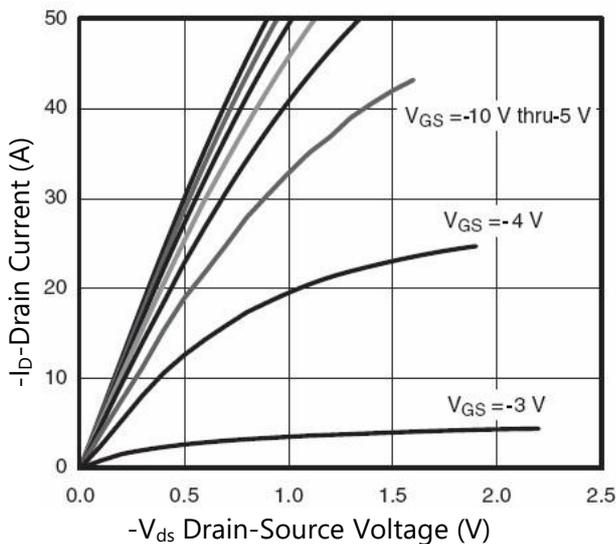
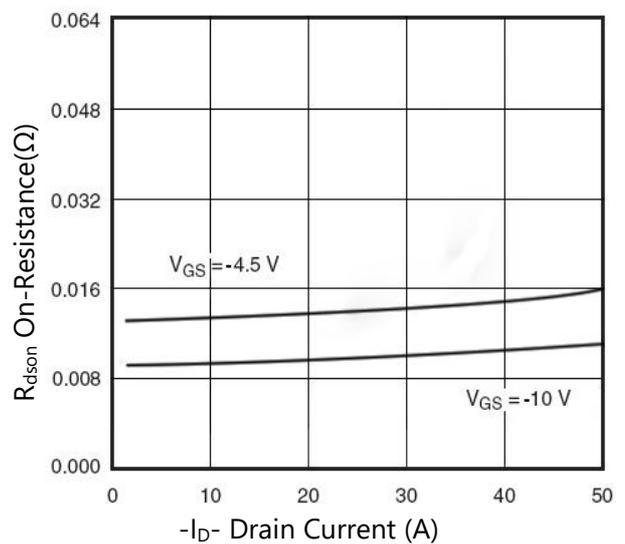


Figure 6. Drain-Source On-Resistance





TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7. Transfer Characteristics

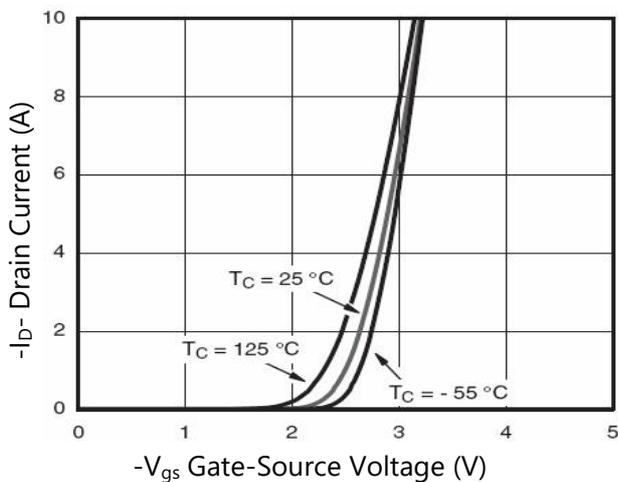


Figure 8. Drain-Source On-Resistance

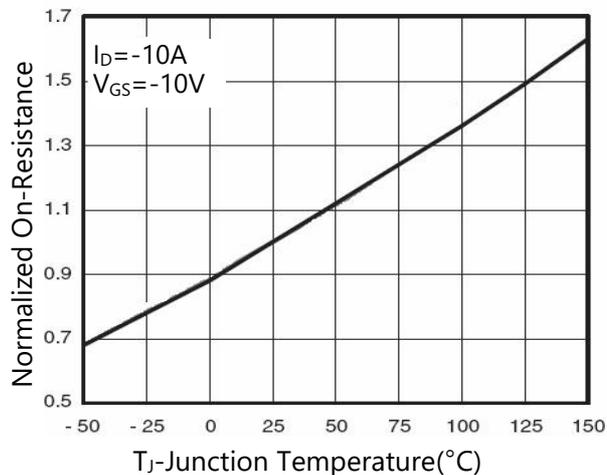


Figure 9. R_{dson} vs V_{gs}

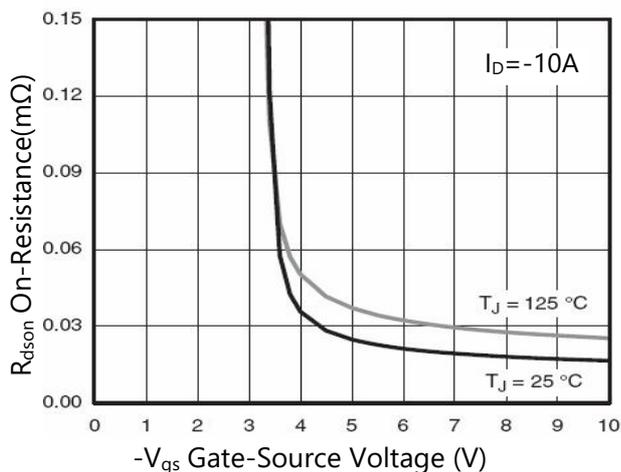


Figure 10. Capacitance vs V_{ds}

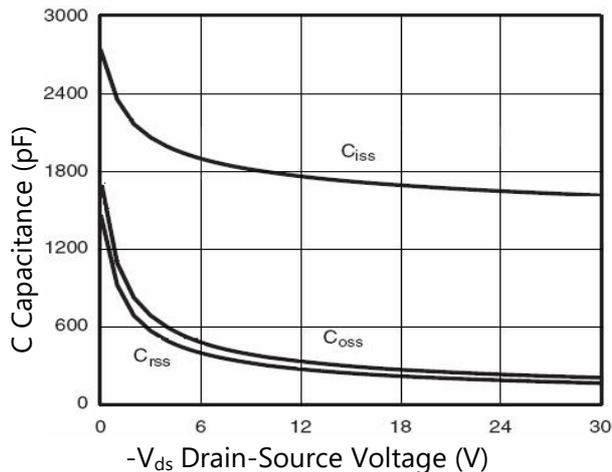


Figure 11. Gate Charge

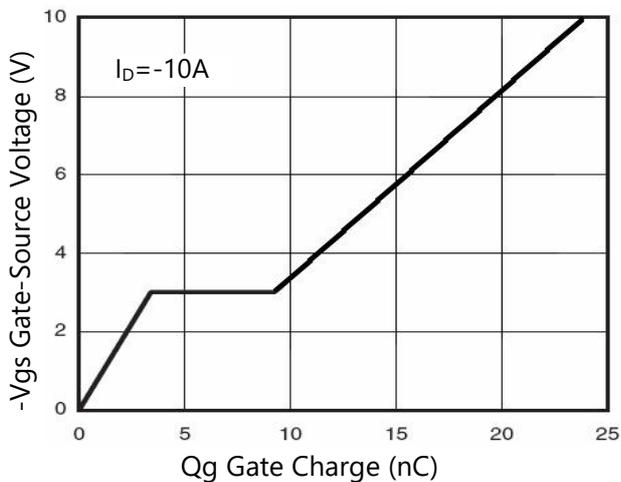
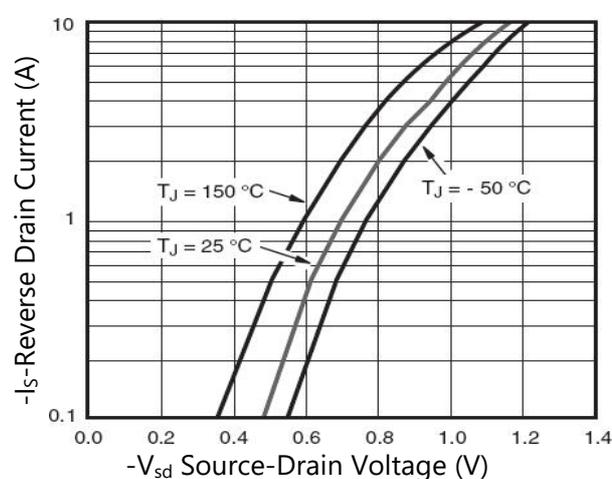


Figure 12. Source- Drain Diode Forward



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 13. Safe Operation Area

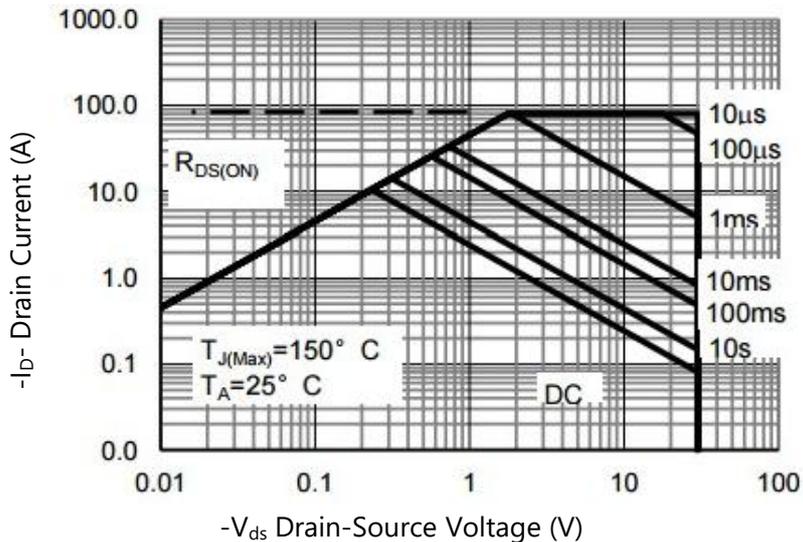
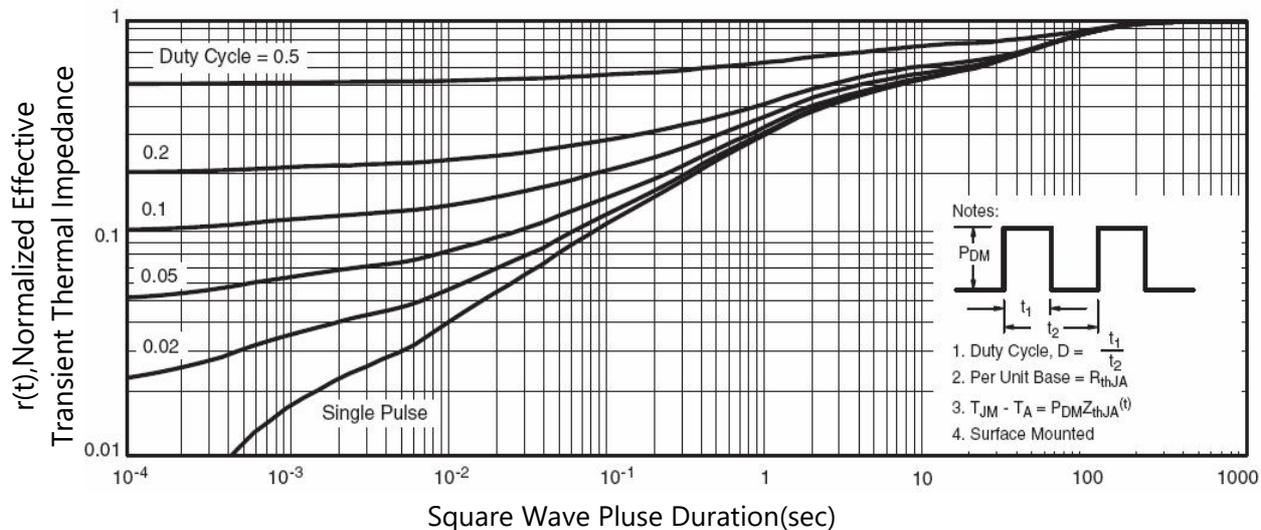
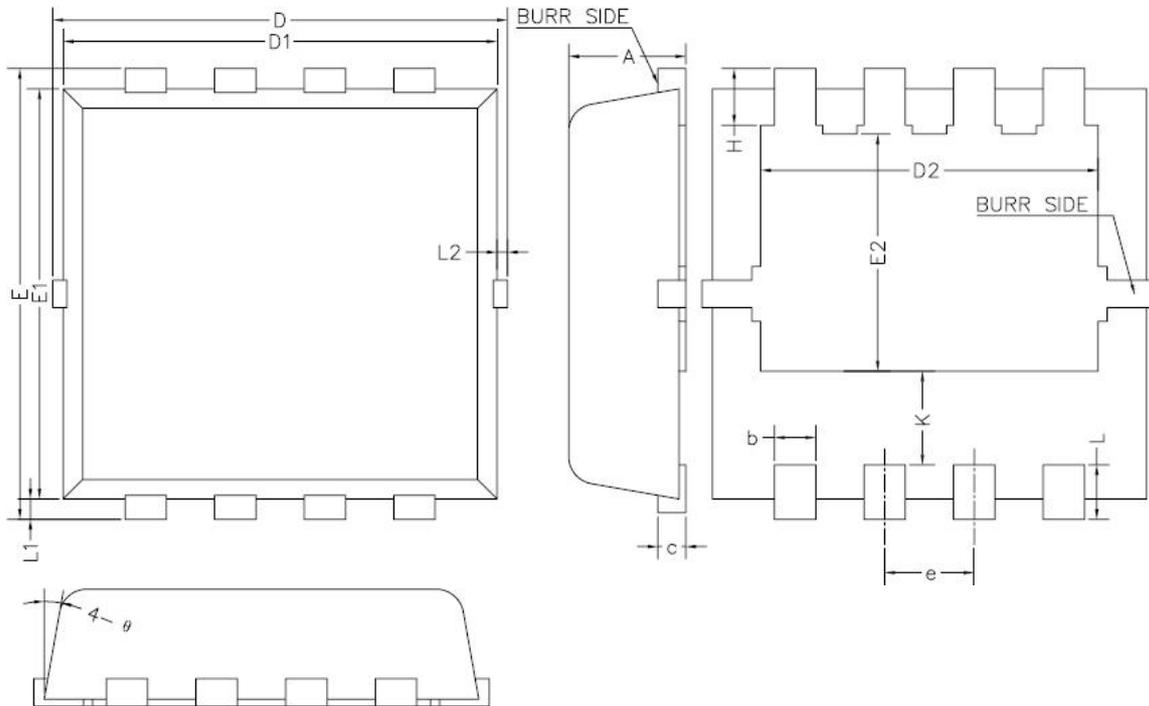


Figure 14. Normalized Maximum Transient Thermal Impedance



PACKAGE INFORMATION

DFN3x3-8L



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.35
c	0.14	0.16	0.20
D	3.10	3.30	3.50
D1	3.05	3.16	3.25
D2	2.35	2.45	2.55
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.64	1.74	1.84
H	0.32	0.42	0.52
K	0.59	0.69	0.79
L	0.25	0.40	0.55
L1	0.10	0.15	0.20
L2			0.16
θ	8°	10°	12°